

Digital transistors (built-in resistors)

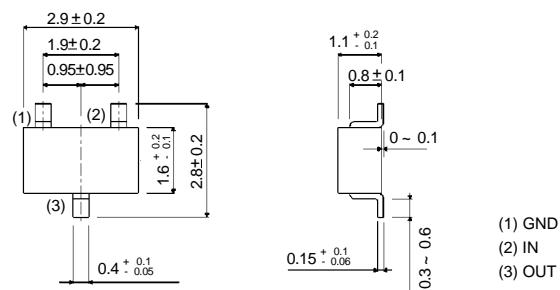
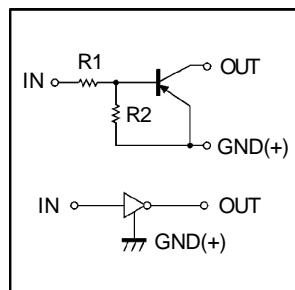
- Features**

- Built-in bias resistors enable the configuration of an inverter circuit without connecting external input resistors (see equivalent circuit).
- The bias resistors consist of thinfilm resistors with complete isolation to allow positive biasing of the input. They also have the advantage of almost completely eliminating parasitic effects.
- Only the on/ off conditions need to be set for operation, making device design easy.

- Structure**

PNP digital transistor (Built-in resistors type)

- Equivalent circuit**



EIAJ: SC—59

- Absolute maximum ratings($T_a=25^\circ C$)

Parameter	symbol	limits		unit
Supply voltage	V_{cc}	-50		V
Input voltage	V_{in}	-40~+6		V
Output current	I_o	-70	mA	
	$I_{C(\text{Max.})}$	-100		
Power dissipation	P_d	200	mW	
Junction temperature	T_j	150		$^\circ C$
Storage temperature	T_{stg}	-55~+150		$^\circ C$

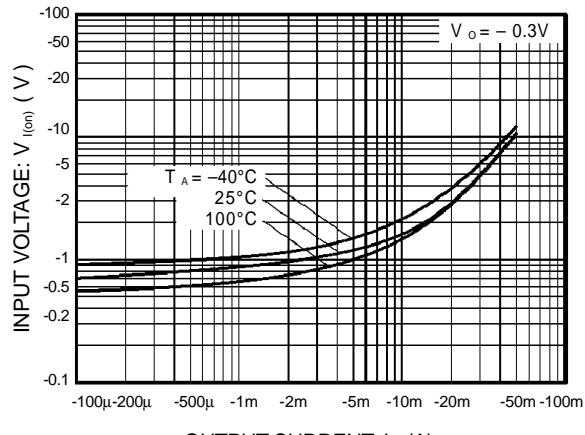
- Electrical characteristics($T_a=25^\circ C$)

Parameter	symbol	Min.	Typ.	Max.	Unit	Conditions
Input voltage	$V_{I(\text{off})}$	—	—	-0.3	V	$V_{cc} = -5V, I_o = -100\mu A$
	$V_{I(\text{on})}$	-1.4	—	—		$V_o = -0.3V, I_o = -1mA$
Output Voltage	$V_{O(\text{on})}$	—	-0.1	-0.3	V	$I_o/I_i = -5mA/-0.25mA$
Input current	I_i	—	—	-0.88	mA	$V_i = -5V$
Output current	$I_{O(\text{off})}$	—	—	-0.5	μA	$V_{cc} = -50V, V_i = 0V$
DC current gain	G_i	68	—	—		$V_o = -5V, I_o = -5mA$
Input resistance	R_i	7	10	13	$K\Omega$	—
Resistance ratio	R_2/R_1	3.7	4.7	5.7	—	—
Transition frequency	f_T	—	250	—	MHz	$V_{ce} = -10V, I_E = 5mA, f = 100MHz^*$

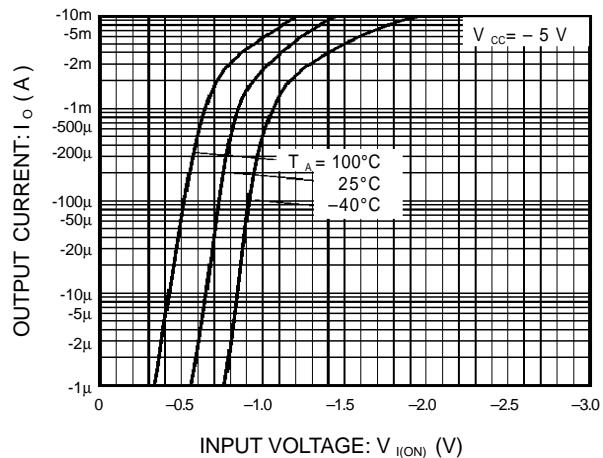
*Transition frequency of the device

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ELECTRICAL CHARACTERISTIC CURVES



**Figure 1. Input voltage vs.output current
(ON characteristics)**



**Figure 2. Output current vs.input voltage
(OFF characteristics)**

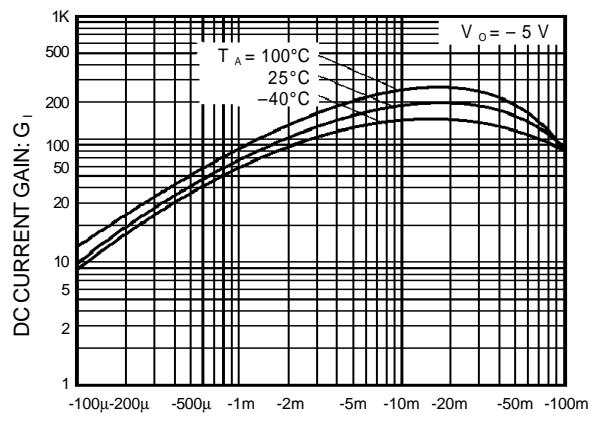


Figure 3. DC current gain vs.output current

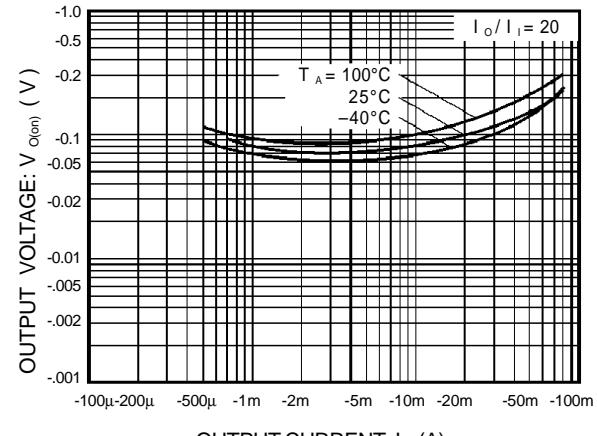


Figure 4. Output voltage vs.output current